# NON-VOLATILE MEMORY DEVICE HAVING DUAL GATE AND METHOD OF FORMING THE SAME

## ABSTRACT OF THE DISCLOSURE

A non-volatile memory device including a control gate pattern having a tunnel insulation pattern, a trap-insulation pattern, a blocking insulation pattern and a control gate electrode, which are stacked on a semiconductor substrate. A selection gate pattern is disposed on the semiconductor substrate at one side of the control gate pattern. A gate insulation pattern is interposed between the selection gate electrode and the semiconductor substrate, and between the selection gate electrode and the control gate pattern. A cell channel region includes a first channel region defined in the semiconductor substrate under the selection gate electrode and a second channel region defined in the semiconductor substrate under the control gate electrode.